

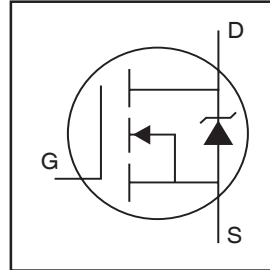
IRLR2908PbF

IRLU2908PbF

HEXFET® Power MOSFET

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free

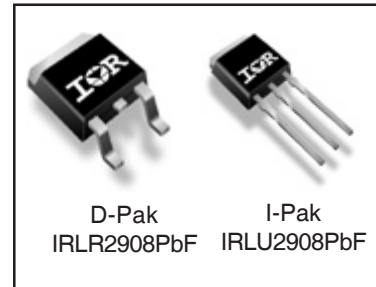


| |
|--------------------------|
| $V_{DSS} = 80V$ |
| $R_{DS(on)} = 28m\Omega$ |
| $I_D = 30A$ |

Description

This HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this HEXFET power MOSFET are a 175°C junction operating temperature, low RθJC, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|--|------------------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) | 39 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (See Fig. 9) | 28 | |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited) | 30 | |
| I_{DM} | Pulsed Drain Current ① | 150 | |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 120 | W |
| | Linear Derating Factor | 0.77 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 16 | V |
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ② | 180 | mJ |
| $E_{AS} (tested)$ | Single Pulse Avalanche Energy Tested Value ② | 250 | |
| I_{AR} | Avalanche Current ① | See Fig.12a,12b,15,16 | A |
| E_{AR} | Repetitive Avalanche Energy ③ | | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 2.3 | V/ns |
| T_J | Operating Junction and | -55 to + 175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds | 300 (1.6mm from case) | |

Thermal Resistance

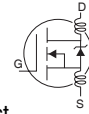
| | Parameter | Typ. | Max. | Units |
|-----------------|-----------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case | — | 1.3 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount) ③ | — | 40 | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 110 | |

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------------------|--------------------------------------|------|-------|------|-------|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 80 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.085 | — | V/°C | Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | 22.5 | 28 | mΩ | $V_{GS} = 10V, I_D = 23A$ ④ |
| | | — | 25 | 30 | | $V_{GS} = 4.5V, I_D = 20A$ ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 1.0 | — | 2.5 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| g_{fs} | Forward Transconductance | 35 | — | — | S | $V_{DS} = 25V, I_D = 23A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | $V_{DS} = 80V, V_{GS} = 0V$ |
| | | — | — | 250 | | $V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 200 | nA | $V_{GS} = 16V$ |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | $V_{GS} = -16V$ |
| Q_g | Total Gate Charge | — | 22 | 33 | nC | $I_D = 23A$ |
| Q_{gs} | Gate-to-Source Charge | — | 6.0 | 9.1 | | $V_{DS} = 64V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | 11 | 17 | | $V_{GS} = 4.5V$ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 12 | — | ns | $V_{DD} = 40V$ |
| t_r | Rise Time | — | 95 | — | | $I_D = 23A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 36 | — | | $R_G = 8.3\Omega$ |
| t_f | Fall Time | — | 55 | — | | $V_{GS} = 4.5V$ ④ |
| L_D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 7.5 | — | | |
| C_{iss} | Input Capacitance | — | 1890 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 260 | — | | $V_{DS} = 25V$ |
| C_{riss} | Reverse Transfer Capacitance | — | 35 | — | | $f = 1.0\text{MHz}$, See Fig. 5 |
| C_{oss} | Output Capacitance | — | 1920 | — | | $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ |
| C_{oss} | Output Capacitance | — | 170 | — | | $V_{GS} = 0V, V_{DS} = 64V, f = 1.0\text{MHz}$ |
| $C_{oss\text{ eff.}}$ | Effective Output Capacitance | — | 310 | — | | $V_{GS} = 0V, V_{DS} = 0V \text{ to } 64V$ |



Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|---|---|------|------|-------|---|
| I_S | Continuous Source Current (Body Diode) | — | — | 39 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | 150 | | |
| V_{SD} | Diode Forward Voltage | — | — | 1.3 | V | $T_J = 25^\circ\text{C}, I_S = 23A, V_{GS} = 0V$ ④ |
| t_{rr} | Reverse Recovery Time | — | 75 | 110 | ns | $T_J = 25^\circ\text{C}, I_F = 23A, V_{DD} = 25V$ |
| Q_{rr} | Reverse Recovery Charge | — | 210 | 310 | nC | $di/dt = 100A/\mu s$ ④ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D) | | | | |

Notes ① through ④ are on page 11

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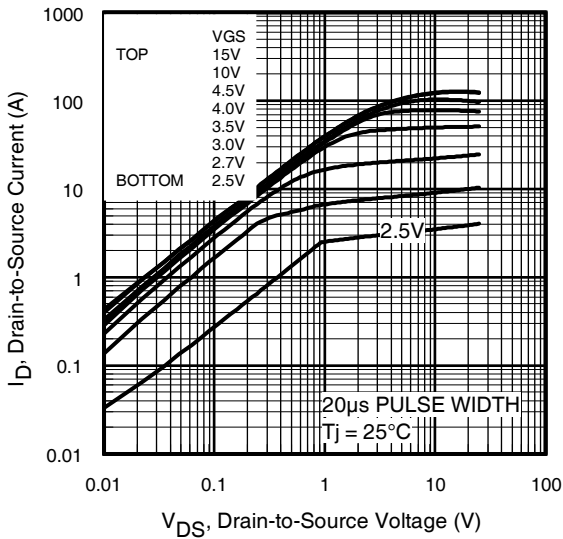


Fig 1. Typical Output Characteristics

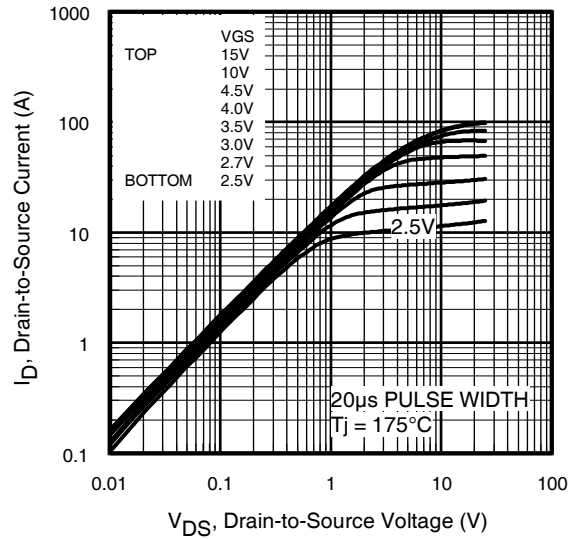


Fig 2. Typical Output Characteristics

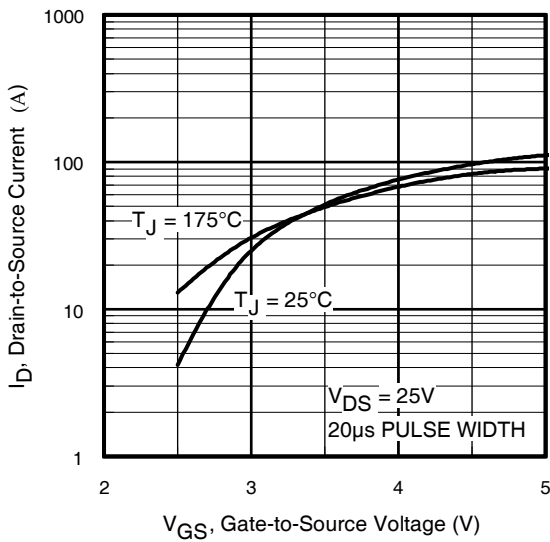


Fig 3. Typical Transfer Characteristics

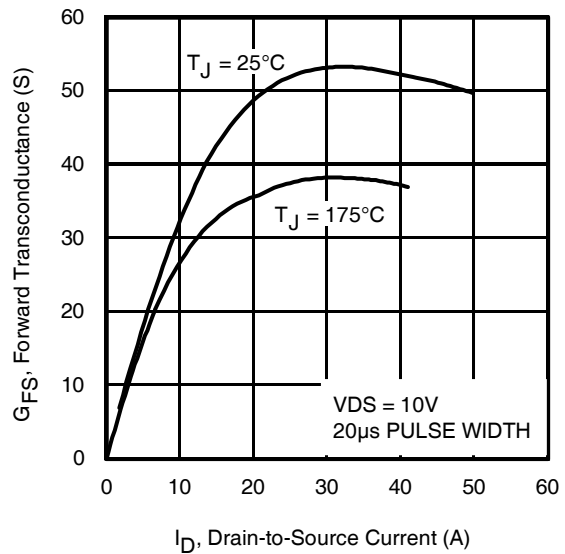


Fig 4. Typical Forward Transconductance vs. Drain Current

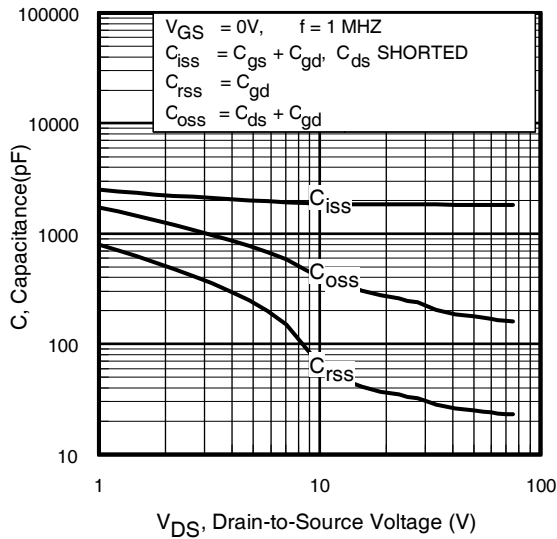


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

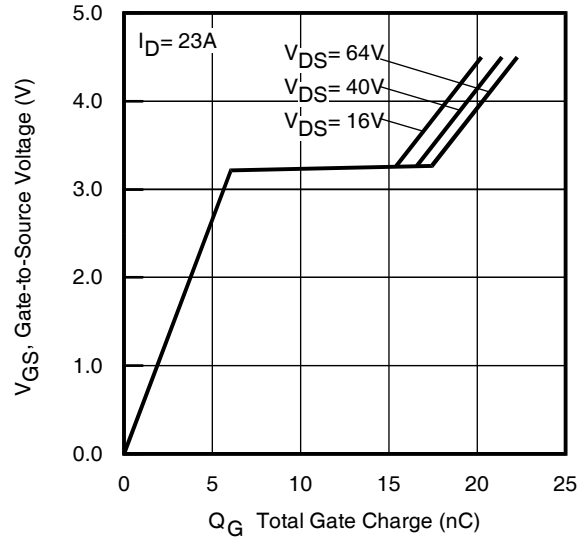


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

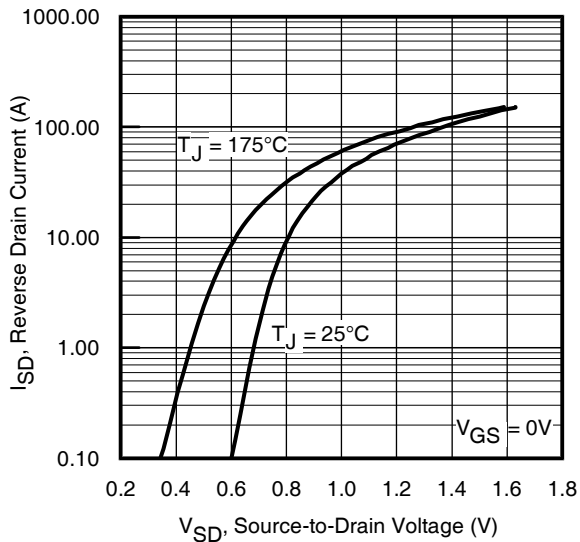


Fig 7. Typical Source-Drain Diode Forward Voltage

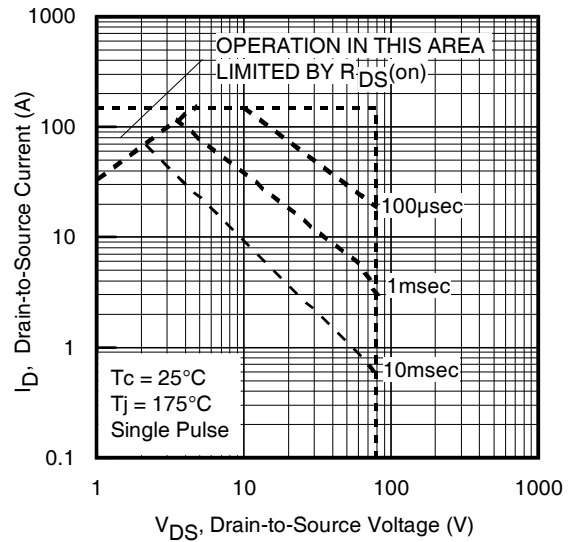


Fig 8. Maximum Safe Operating Area

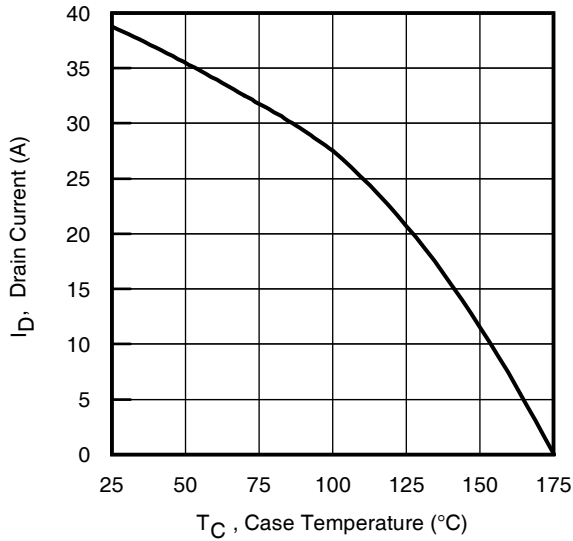


Fig 9. Maximum Drain Current vs. Case Temperature

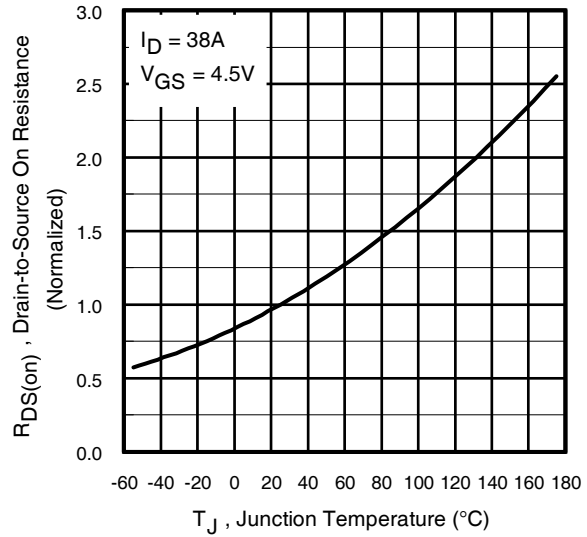


Fig 10. Normalized On-Resistance vs. Temperature

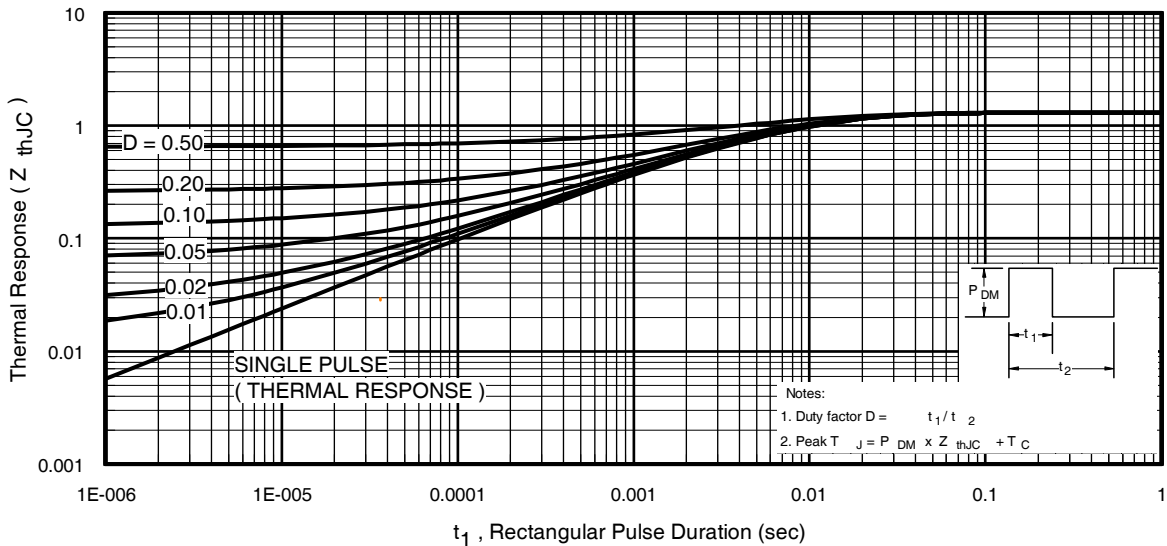


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms



Fig 13a. Basic Gate Charge Waveform



Fig 13b. Gate Charge Test Circuit

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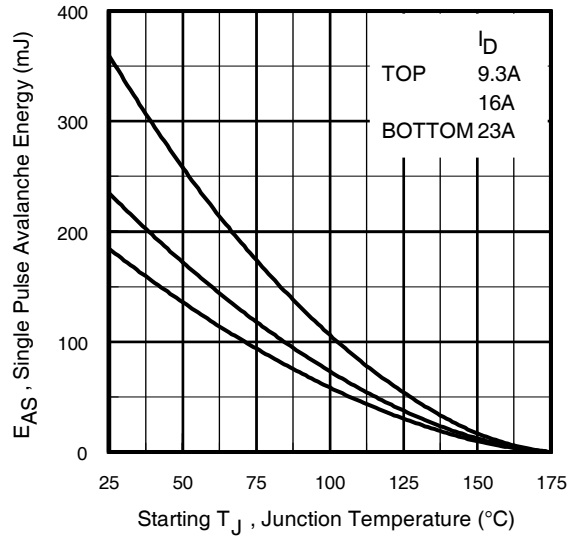


Fig 12c. Maximum Avalanche Energy vs. Drain Current

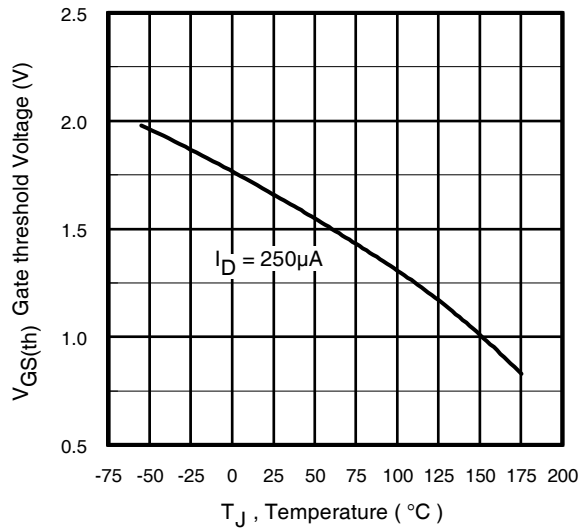


Fig 14. Threshold Voltage vs. Temperature

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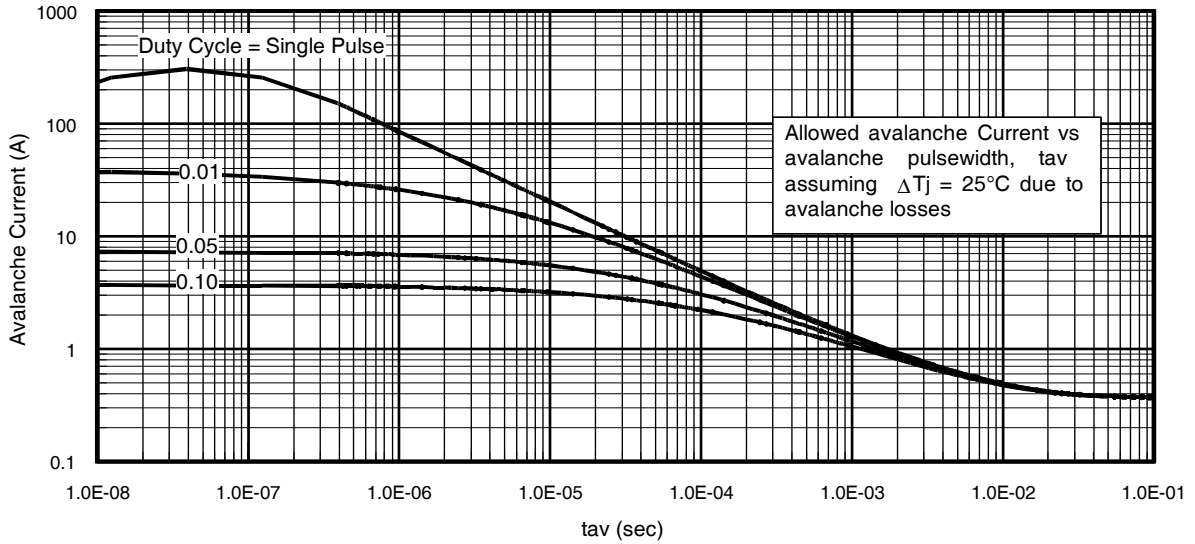


Fig 15. Typical Avalanche Current vs.Pulsewidth

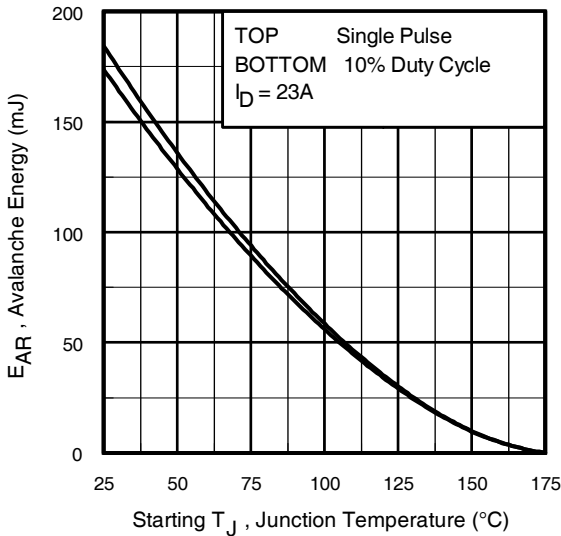


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

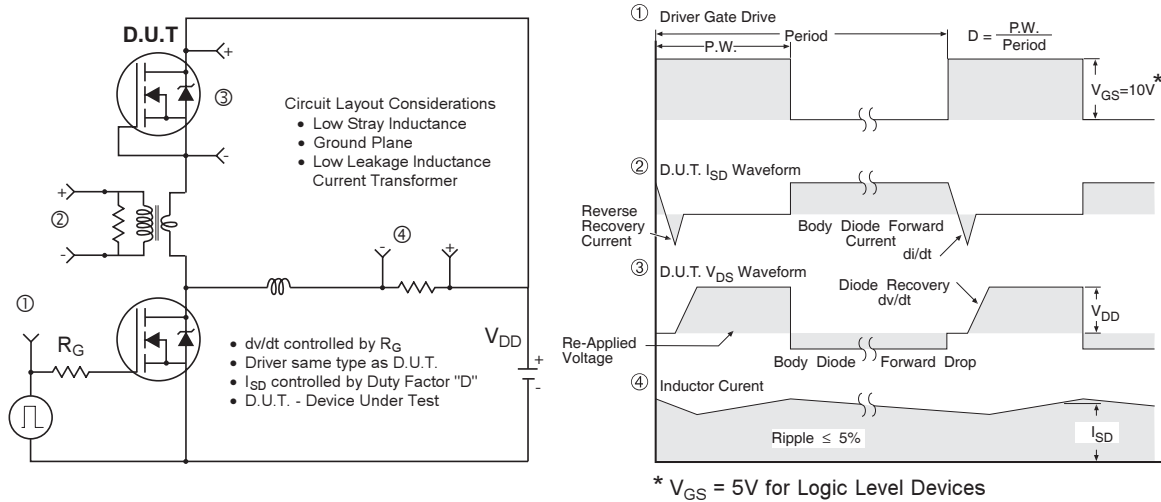


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

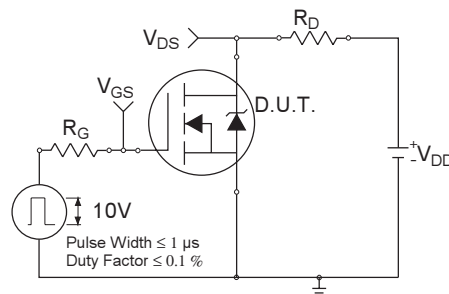


Fig 18a. Switching Time Test Circuit

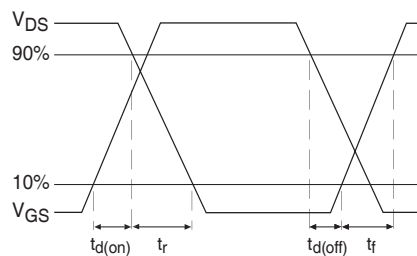
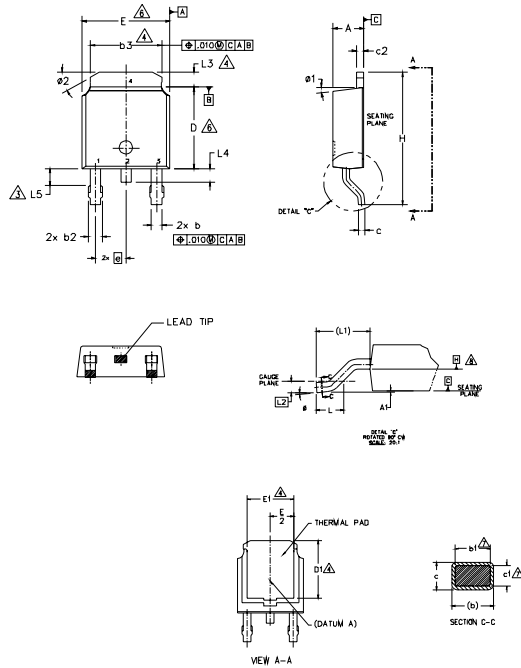


Fig 18b. Switching Time Waveforms

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
 - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|-----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | .086 | .094 | |
| A1 | - | 0.13 | - | .005 | |
| b | 0.64 | 0.89 | .025 | .035 | |
| b1 | 0.65 | 0.79 | .025 | .031 | 7 |
| b2 | 0.76 | 1.14 | .030 | .045 | |
| b3 | 4.95 | 5.46 | .195 | .215 | 4 |
| c | 0.46 | 0.61 | .018 | .024 | |
| c1 | 0.41 | 0.56 | .016 | .022 | 7 |
| c2 | 0.46 | 0.89 | .018 | .035 | |
| D | 5.97 | 6.22 | .235 | .245 | 6 |
| D1 | 5.21 | - | .205 | - | 4 |
| E | 6.35 | 6.73 | .250 | .265 | 6 |
| E1 | 4.32 | - | .170 | - | 4 |
| e | 2.29 BSC | | .090 BSC | | |
| H | 9.40 | 10.41 | .370 | .410 | |
| L | 1.40 | 1.78 | .055 | .070 | |
| L1 | 2.74 BSC | | .108 REF. | | |
| L2 | 0.51 BSC | | .020 BSC | | |
| L3 | 0.89 | 1.27 | .035 | .050 | 4 |
| L4 | - | 1.02 | - | .040 | |
| L5 | 1.14 | 1.52 | .045 | .060 | 3 |
| phi | 0" | 10" | 0" | 10" | |
| phi1 | 0" | 15" | 0" | 15" | |
| phi2 | 25" | 35" | 25" | 35" | |

LEAD ASSIGNMENTS

- HEXFET**
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120 WITH ASSEMBLY LOT CODE 1234 ASSEMBLED ON WW 16, 2001 IN THE ASSEMBLY LINE "A"

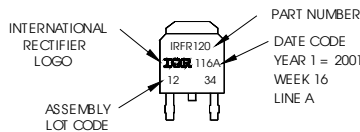
Note: "P" in assembly line position indicates "Lead-Free"

"P" in assembly line position indicates "Lead-Free" qualification to the consumer-level

OR

INTERNATIONAL RECTIFIER LOGO

ASSEMBLY LOT CODE



PART NUMBER

DATE CODE

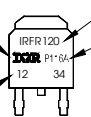
YEAR 1 = 2001

WEEK 16

LINE A

INTERNATIONAL RECTIFIER LOGO

ASSEMBLY LOT CODE



PART NUMBER

DATE CODE

P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)

P̄ = DESIGNATES LEAD-FREE PRODUCT QUALIFIED TO THE CONSUMER LEVEL (OPTIONAL)

YEAR 1 = 2001

WEEK 16

A = ASSEMBLY SITE CODE

Notes:

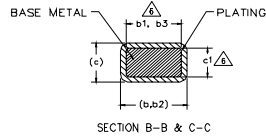
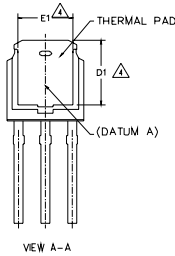
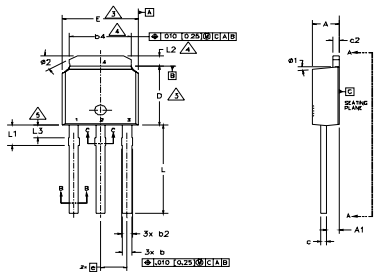
1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/automotive/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

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International
IR Rectifier

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
 - △ DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - △ THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
 - △ LEAD DIMENSION UNCONTROLLED IN L3.
 - △ DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
 - 8.- CONTROLLING DIMENSION : INCHES.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|------|----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 2.18 | 2.39 | .086 | .094 | |
| A1 | 0.89 | 1.14 | .035 | .045 | |
| b | 0.64 | 0.89 | .025 | .035 | |
| b1 | 0.65 | 0.79 | .025 | .031 | 6 |
| b2 | 0.76 | 1.14 | .030 | .045 | |
| b3 | 0.76 | 1.04 | .030 | .041 | 6 |
| b4 | 4.95 | 5.46 | .195 | .215 | 4 |
| c | 0.46 | 0.61 | .018 | .024 | |
| c1 | 0.41 | 0.56 | .016 | .022 | 6 |
| c2 | 0.46 | 0.89 | .018 | .035 | |
| D | 5.97 | 6.22 | .235 | .245 | 3 |
| D1 | 5.21 | - | .205 | - | 4 |
| E | 6.35 | 6.73 | .250 | .265 | 3 |
| E1 | 4.32 | - | .170 | - | 4 |
| e | 2.29 BSC | | .090 BSC | | |
| L | 8.89 | 9.65 | .350 | .380 | |
| L1 | 1.91 | 2.29 | .045 | .090 | 4 |
| L2 | 0.89 | 1.27 | .035 | .050 | |
| L3 | 1.14 | 1.52 | .045 | .060 | 5 |
| ø1 | 0" | 15" | 0" | 15" | |
| ø2 | 25" | 35" | 25" | 35" | |

LEAD ASSIGNMENTS

HEXFET

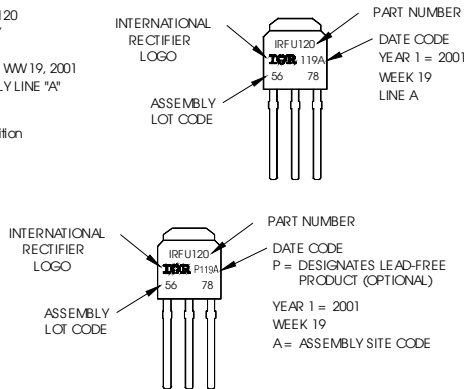
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW19, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates Lead-Free!

OR

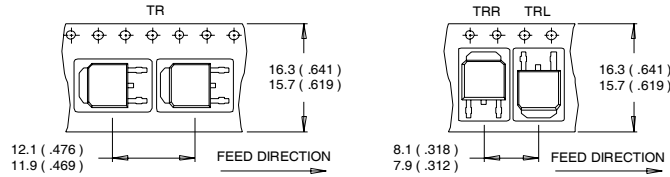


Notes:

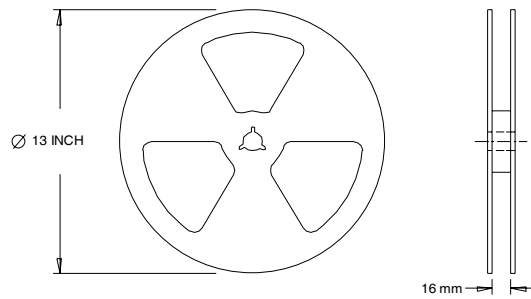
1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.71\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 23\text{A}$, $V_{GS} = 10\text{V}$. Part not recommended for use above this value.
- ③ $I_{SD} \leq 23\text{A}$, $di/dt \leq 400\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 1.0\text{ms}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ This value determined from sample failure population. 100% tested to this value in production.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 10/2010